



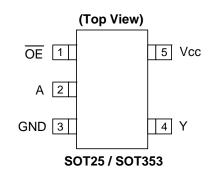
#### Description

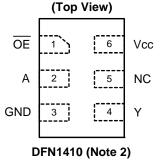
The 74LVC1G125 is a single non-inverting buffer/bus driver with a 3-state output. The output enters a high impedance state when a HIGH-level is applied to the output enable  $\overline{(OE)}$ pin. The device is designed for operation with a power supply range of 1.65V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using I<sub>OFF</sub>. The I<sub>OFF</sub> circuitry disables the output preventing damaging current backflow when the device is powered down.

#### **Features**

- Wide Supply Voltage Range from 1.65 to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Tested per JESD 22
  Exceeds 200-V Machine Model (A115-A)
  Exceeds 2000-V Human Body Model (A114-A)
- Latch-Up Exceeds 100mA per JESD 78, Class II Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options
- Direct Interface with TTL Levels
- SOT25, SOT353, and DFN1410: Assembled with "Green" Molding Compound (no Br, Sb)
- Lead Free Finish/ RoHS Compliant (Note 1)

#### **Pin Assignments**





#### Applications

- Voltage Level Shifting
- Bus Driver / Repeater
- Power Down Signal Isolation
- General Purpose Logic
- Wide array of products such as.
  - PCs, networking, notebooks, netbooks, PDAs
  - o Computer peripherals, hard drives, CD/DVD ROM
  - o TV, DVD, DVR, set top box
  - o Cell Phones, Personal Navigation / GPS
  - o MP3 players ,Cameras, Video Recorders

Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead\_free.html.

2. Pin 2 and pin 5 of the DFN1410 package are internally connected.

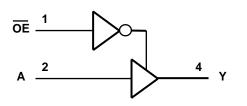


## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

## **Pin Descriptions**

Pin Name	Description
ŌĒ	Output Enable
А	Data Input
GND	Ground
Y	Data Output
Vcc	Supply Voltage
NC	No Connection

## Logic Diagram



## **Function Table**

Inp	Output	
OE	Α	Y
L	Н	Н
L	L	L
н	Х	Z



## Absolute Maximum Ratings (Note 3)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V <sub>CC</sub>	Supply Voltage Range	-0.5 to 6.5	V
VI	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or I <sub>OFF</sub> state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Clamp Current V <sub>I</sub> <0	-50	mA
I <sub>OK</sub>	Output Clamp Current	-50	mA
lo	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T <sub>STG</sub>	Storage Temperature	-65 to 150	°C

Notes: 3. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.



## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

## **Recommended Operating Conditions (Note 4)**

Symbol		Parameter	Min	Max	Unit
		Operating	1.65	5.5	V
V <sub>CC</sub>	Operating Voltage	Data retention only	1.5		V
		V <sub>CC</sub> = 1.65V to 1.95V	$0.65 \times V_{CC}$		
N/	High lovel logut Veltage	$V_{CC} = 2.3V$ to 2.7V	1.7		V
VIH	nigh-level input voltage	$V_{CC} = 3V$ to 3.6V	2		V
		V <sub>CC</sub> = 4.5V to 5.5V	0.7 X V <sub>CC</sub>		
		V <sub>CC</sub> = 1.65V to 1.95V		0.35 X V <sub>CC</sub>	
	La la all'an ta altera	V <sub>CC</sub> = 2.3V to 2.7V		0.7	
VIL	V <sub>IL</sub> Low-level input voltage	V <sub>CC</sub> = 3V to 3.6V		0.8	V
		V <sub>CC</sub> = 4.5V to 5.5V		0.3 X V <sub>CC</sub>	
VI	Input Voltage		0	5.5	V
Vo	Output Voltage		0	V <sub>CC</sub>	V
		V <sub>CC</sub> = 1.65V			
		V <sub>CC</sub> = 2.3V		-8	
I <sub>OH</sub>	High-level output current			-16	mA
		$V_{CC} = 3V$		-24	
	Low-level input voltage Input Voltage Output Voltage High-level output current Low-level output current	$V_{CC} = 4.5V$		-32	
		V <sub>CC</sub> = 1.65V		4	
		$V_{CC} = 2.3 V$		8	
I <sub>OL</sub>	Low-level output current	$V_{CC} = 3V$		16	mA
		VCC = 3V		24	
		$V_{CC} = 4.5V$		32	
	Les Constitues de la Call	$V_{CC} = 1.8V \pm 0.15V, 2.5V \pm 0.2V$		20	
Δt/ΔV	-	$V_{CC} = 3.3V \pm 0.3V$		10	ns/V
		$V_{CC} = 5V \pm 0.5V$		5	
T <sub>A</sub>	Operating free-air temperature		-40	85	٥C

Notes: 4. Unused inputs should be held at Vcc or Ground.



## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

### Electrical Characteristics (All typical values are at Vcc = 3.3V, T<sub>A</sub> = $25^{\circ}$ C)

Symbol	Parameter	Test Conditions	Vcc	Min	Тур.	Max	Unit	
		I <sub>OH</sub> = -100μA	1.65V to 5.5V	V <sub>CC</sub> – 0.1				
		I <sub>OH</sub> = -4mA	1.65V	1.2				
	High Level Output	I <sub>OH</sub> = -8mA	2.3V	1.9				
V <sub>OH</sub>	Voltage	I <sub>OH</sub> = -16mA	0)/	2.4			V	
		I <sub>OH</sub> = -24mA	3V	2.3				
	Voltage      DL    High-level Input Voltage      I    Input Current      FF    Power Down Leakage      Current    Z      Z    Z State Leakage Current      CC    Supply Current      Ci    Input Capacitance      Thermal Resistance    Thermal Resistance	I <sub>OH</sub> = -32mA	4.5V	3.8				
		I <sub>OL</sub> = 100μΑ	1.65V to 5.5V			0.1		
		$I_{OL} = 4mA$	1.65V			0.45		
		I <sub>OL</sub> = 8mA	2.3V			0.3		
VOL	High-level Input Voltage	I <sub>OL</sub> = 16mA				0.4	V	
		I <sub>OL</sub> = 24mA	3V			0.55		
		I <sub>OL</sub> = 32mA	4.5V			0.55		
lı	Input Current	$V_I = 5.5V$ or GND	0 to 5.5V			± 5	μA	
I <sub>OFF</sub>		V <sub>I</sub> or V <sub>O</sub> = 5.5V	0			± 10	μA	
I <sub>OZ</sub>	Z State Leakage Current	V <sub>O</sub> =0 to 5.5V	3.6V			± 10	μA	
I <sub>CC</sub>	Supply Current	V <sub>I</sub> = 5.5V of GND I <sub>O</sub> =0	1.65V to 5.5V			10	μA	
ΔI <sub>CC</sub>	Additional Supply Current	One input at $V_{CC}$ – 0.6 V Other inputs at $V_{CC}$ or GND	3V to 5.5V			500	μA	
Ci	Input Capacitance	$V_i = V_{CC} - or GND$	3.3		4		pF	
	Thormal Posistance	SOT25	(Note 5)		204		°C/W	
$\theta_{JA}$	Junction-to-Ambient	SOT353	(Note 5)		371		°C/W	
		DFN1410	(Note 5)		430		°C/W	
	Thermal Resistance	SOT25	(Note 5)		52		°C/W	
θ <sub>JC</sub>	Junction-to-Case	SOT353	(Note 5)		143		°C/W	
		DFN1410	(Note 5)		190		°C/W	

Over recommended free-air temperature range (unless otherwise noted)

Notes: 5. Test condition for SOT25, SOT353, and DFN1410: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



## **Switching Characteristics**

F	Parameter	Parameter	From	-	TO	Vcc = ± 0.	1.8 V 15V	Vcc = ± 0	2.5 V .2V	Vcc = ± 0	3.3 V .3V		= 5 V 0.5V	Unit
		(Input)	ut) (OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max			
	t <sub>pd</sub>	А	Y	1.9	6.9	0.7	4.6	0.6	3.7	0.5	3.4	ns		

Over recommended free-air temperature range, CL = 15pF (see Figure 1)

#### Over recommended free-air temperature range, CL = 30 or 50pF as noted (see Figure 2)

Parameter	From (Input)			TO	Vcc = ± 0.	1.8 V 15V	Vcc = ± 0	2.5 V .2V	Vcc = ± 0	3.3 V .3V		= 5 V 0.5V	Unit
		(OUTPUT)	Min	Max	Min	Max	Min	Мах	Min	Max			
t <sub>pd</sub>	А	Y	2.8	9.0	1.2	5.5	1.0	4.5	1.0	4.0	ns		
t <sub>en</sub>	ŌĒ	Y	2.8	10.1	1.5	6.6	1.0	5.3	1.0	5.0	ns		
t <sub>dis</sub>	ŌĒ	Y	1.3	9.2	1.0	5.5	1.0	5.5	1.0	4.2	ns		

### **Operating Characteristics**

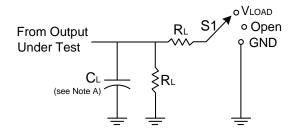
T<sub>A</sub> = 25 °C

Parameter		Test	Vcc = 1.8 V	Vcc = 2.5 V	Vcc = 3.3 V	Vcc = 5 V	Unit	
			Conditions	TYP	ТҮР	TYP	ТҮР	
0	Power	Outputs enabled	f = 10 MHz	19	19	19	21	~F
C <sub>pd</sub>	dissipation capacitance	Outputs disabled		2	2	3	4	pF



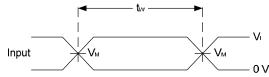
## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

#### **Parameter Measurement Information**

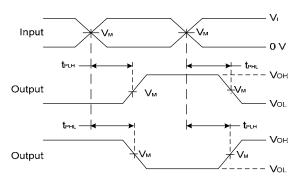


TEST	S1
t <sub>PLH</sub> /t <sub>PHL</sub>	Open
t <sub>PLZ</sub> /t <sub>PZL</sub>	Vload
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

Vcc	Inputs		V <sub>M</sub>	V <sub>LOAD</sub>	C∟	RL	V۵
Vi t <sub>r</sub> /t <sub>f</sub>		▼ IVI	• LOAD	υL	ι.ς	• A	
1.8V±0.15V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	15pF	1MΩ	0.15V
2.5V±0.2V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	15pF	1MΩ	0.15V
3.3V±0.3V	3V	≤2.5ns	1.5V	6V	15pF	1MΩ	0.3V
5V±0.5V	V <sub>CC</sub>	≤2.5ns	V <sub>CC</sub> /2	$2 X V_{CC}$	15pF	1MΩ	0.3V







Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

#### ٧ı Output Vм Vм Control οv Output t⊧zı. → t<sub>PL2</sub> VLOAD/2 Waveform 1 S1 at VLOAD VOL + V (see Note B) Vol t⊳zн → → ← t<sub>PHZ</sub> Output Vон Waveform 2 Vон - V<sub>4</sub> ∠∧™ S1 at GND (see Note B) 6 OV

#### Voltage Waveform Enable and Disable Times Low and High Level Enabling

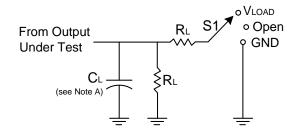
#### Figure 1. Load Circuit and Voltage Waveforms

- Notes: A. Includes test lead and test apparatus capacitance.
  - B. All pulses are supplied at pulse repetition rate  $\leq$  10 MHz.
    - C. Inputs are measured separately one transition per measurement.
    - D.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis.}$
    - E.  $t_{\text{PZL}}$  and  $t_{\text{PZH}}$  are the same as  $t_{\text{EN}}$
    - F.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{PD.}$



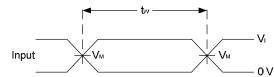
## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

#### Parameter Measurement Information (Continued)

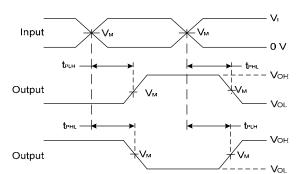


TEST	S1
t <sub>PLH</sub> /t <sub>PHL</sub>	Open
t <sub>PLZ</sub> /t <sub>PZL</sub>	Vload
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

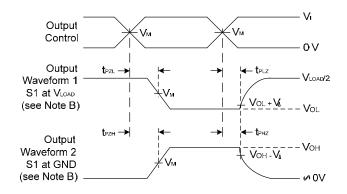
Vcc	Inputs		V <sub>M</sub>	V <sub>LOAD</sub>	CL	RL	VA
	VI	t <sub>r</sub> /t <sub>f</sub>	• 101	LOAD	υL		• 🛆
1.8V±0.15V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	30pF	1KΩ	0.15V
2.5V±0.2V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	30pF	500Ω	0.15V
3.3V±0.3V	3V	≤2.5ns	1.5V	6V	50pF	500Ω	0.3V
5V±0.5V	V <sub>CC</sub>	≤2.5ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	50pF	500Ω	0.3V



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs



#### Voltage Waveform Enable and Disable Times Low and High Level Enabling

Figure 2. Load Circuit and Voltage Waveforms

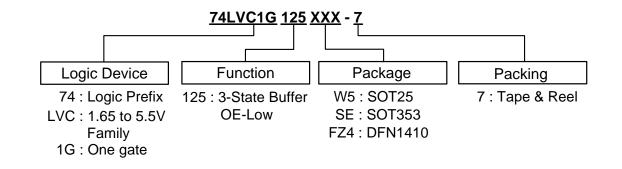
Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate  $\leq$  10 MHz.
- C. Inputs are measured separately one transition per measurement.
- D.  $t_{\text{PLZ}}$  and  $t_{\text{PHZ}}$  are the same as  $t_{\text{dis.}}$
- E.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{ENO}$
- F.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{PD.}$



## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

### **Ordering Information**



	Device	Package Code	Packaging (Note 6)	7" Tape and Reel	
				Quantity	Part Number Suffix
Lead-free Green	74LVC1G125W5-7	W5	SOT25	3000/Tape & Reel	-7
Case over Green		SE	SOT353	3000/Tape & Reel	-7
Pb,	74LVC1G125FZ4-7	FZ4	DFN1410	5000/Tape & Reel	-7

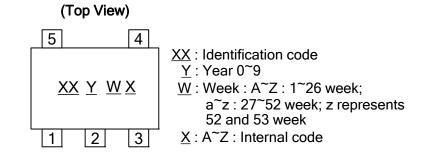
Notes: 6. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.





### **Marking Information**

#### (1) SOT25 and SOT353



Part Number	Package	Identification Code	
74LVC1G125W5	SOT25	UY	
74LVC1G125SE	SOT353	UY	

#### (2) DFN1410

#### (Top View)

		XX : Identification Code			
	<u>XX</u>	$\underline{Y}$ : Year : 0~9			
	YWX	<u>W</u> : Week : A~Z : 1~26 week;			
	•	a~z : 27~52 week; z represents			
52 and 53 week					
	X : A~Z : Internal code				

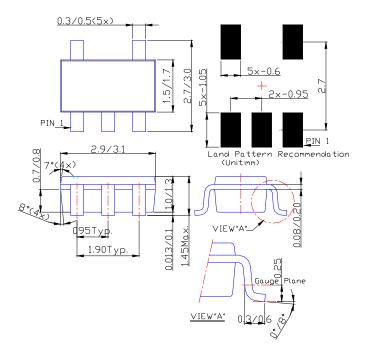
Part Number	Package	Identification Code	
74LVC1G125FZ4	DFN1410	UY	



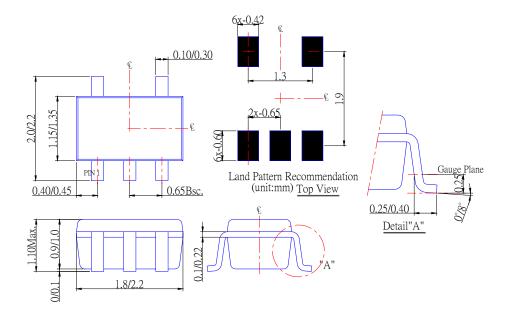
## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

### Package Outline Dimensions (All Dimensions in mm)

#### (1) Package Type: SOT25



#### (2) Package Type: SOT353



NEW PRODUCT

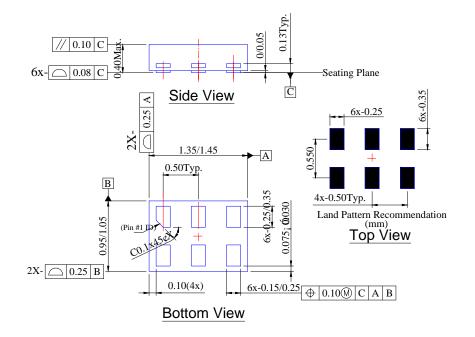
#### 74LVC1G125 Document number: DS32202 Rev. 2 - 2



## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

### Package Outline Dimensions (Continued)

#### (3) Package Type: DFN1410

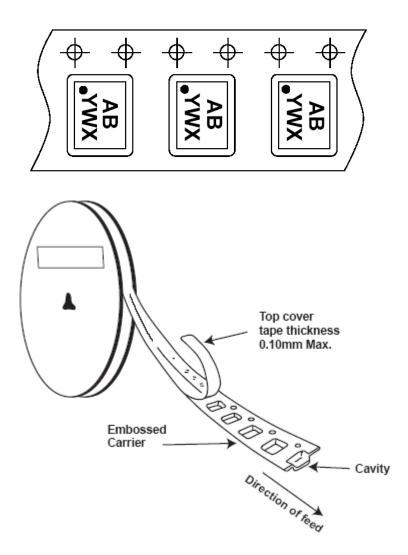




## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

### Taping Orientation (Note 7)

#### For DFN1410







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